a fifth region having the second conductivity, disposed in the first section of the layer, extending deeper into the layer than the body region, and contiguous with the body region; and

wherein the layer composes a transistor drain region.

38. A semiconductor die, comprising:

a side;

a layer having a first conductivity and bounded by the side;

an inner section of the layer having a first surface;

a perimeter section of the layer contiguous with and disposed between the inner section and the side and having a second surface that is offset from the first surface;

a guard region having a second conductivity, disposed in the perimeter section of the layer, and contiguous with the second surface; and

column regions having the second conductivity, disposed in the guard region, contiguous with the second surface, and extending deeper into the layer than the guard region.

39. The semiconductor die of claim 38 wherein the guard region is spaced from the side.

40. The semiconductor die of claim 38, further comprising a contact region having the first conductivity, disposed in the perimeter section of the layer, and contiguous with the side.

41. The semiconductor die of claim 38, further comprising an edge that extends between the first and second surfaces and that is substantially normal to one of the first and second surfaces.

42. A circuit, comprising:

a semiconductor device including a semiconductor die comprising,

a side,

a layer having a first conductivity and bounded by the side,

an inner section of the layer having a first surface,

a perimeter section of the layer contiguous with and disposed between the inner section and the side and having a second surface that is offset from the first surface,

a guard region having a second conductivity, disposed in the perimeter section of the layer, and contiguous with the second surface, and

column regions having the second conductivity, disposed in the guard region, contiguous with the second surface, and extending deeper into the layer than the guard region; and

an electronic component coupled to the semiconductor device.

43. An electronic system, comprising:

a circuit, comprising,

a semiconductor device including a semiconductor die comprising,

a side,

a layer having a first conductivity and bounded by the side,

an inner section of the layer having a first surface,

a perimeter section of the layer contiguous with and disposed between the inner section and the side and having a second surface that is offset from the first surface,

a guard region having a second conductivity, disposed in the perimeter section of the layer, and contiguous with the second surface, and

column regions having the second conductivity, disposed in the guard region, contiguous with the second surface, and extending deeper into the layer than the guard region; and an electronic component coupled to the semiconductor device.

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